

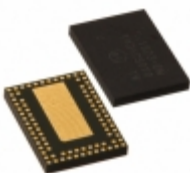



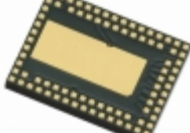
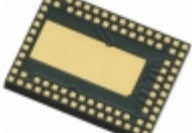

	<p><b>SI1025X-T1-E3</b></p>
	<p><b>Hersteller-Teilenummer:</b> SI1025X-T1-E3</p> <p><b>Hersteller / Marke:</b> Vishay / Siliconix</p> <p><b>Teil der Beschreibung:</b> MOSFET 2P-CH 60V 0.19A SOT563F</p> <p><b>Datenblätter:</b>  <a href="#">SI1025X-T1-E3.pdf</a></p> <p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 285582 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

### Spezifikationen

Teilenummer	SI1025X-T1-E3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET 2P-CH 60V 0.19A SOT563F
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	285582 pcs Stock
Serie	TrenchFET®
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Leistung - max	250mW
Verpackung / Gehäuse	SOT-563, SOT-666
Supplier Device-Gehäuse	SC-89-6
Typ FET	2 P-Channel (Dual)
FET-Merkmal	Logic Level Gate
Drain-Source-Spannung (Vdss)	60V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	190mA
Rds On (Max) @ Id, Vgs	4 Ohm @ 500mA, 10V
VGS (th) (Max) @ Id	3V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	1.7nC @ 15V
Eingabekapazität (Ciss) (Max) @ Vds	23pF @ 25V
Verpackung	Tape & Reel (TR)

SI1025X-T1-E3 ist neu im Original, Suche SI1025X-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI1025X-T1-E3 Vishay / Siliconix mit Garantie und Vertrauen.  
Anfrage SI1025X-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

 <b>SI1025X</b> VISHAY SI1025X VISHAY	 <b>SI1026-A-GMR</b> Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 85-VFLGA	 <b>SI1026-A-GM</b> Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 85-VFLGA	 <b>SI1025X-T1-GE3</b> Vishay / Siliconix MOSFET 2P-CH 60V 0.19A SC-89
 <b>SI1025X-T1-E3</b> Electro-Films (EFI) / Vishay MOSFET 2P-CH 60V 0.19A SOT563F	 <b>SI1025-B-GM3</b> Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 85-VFLGA	 <b>SI1025-B-GMR</b> Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 85-VFLGA	 <b>SI1025X-T1</b> XX SI1025X-T1 XX

### heiße Teile

Mehr

SI1021R-T1	SI1021R-T1-E3	SI1021R-T1-E3	SI1022R-T1	SI1022R-T1-E3
SI1022R-T1-E3	SI1022R-T1-GE3	SI1022R-T1-GE3	SI1022R-T1-E3	SI1023CX-T1-GE3
SI1023CX-T1-GE3	SI1023X-T1	SI1023X-T1-E3	SI1023X-T1-E3	SI1023X-T1-GE3
SI1023X-T1-GE3	SI1024-T1	SI1024X-T1	SI1024X-T1-E3	SI1024X-T1-E3
SI1024X-T1-GE3	SI1024X-T1-GE3	SI1024X-T1-GE3	SI1025X-T1	SI1025X-T1-E3
SI1026X-T1	SI1026X-T1-E3	SI1026X-T1-E3	SI1026X-T1-GE3	SI1026X-T1-GE3
SI1028X-T1-GE3	SI1028X-T1-GE3	SI1029X-T1-GE3	SI1029X-T1-GE3	SI1031R-T1
SI1031R-T1-E3	SI1031R-T1-E3	SI1031R-T1-GE3	SI1031R-T1-GE3	SI1031X-T1
SI1031X-T1-E3	SI1031X-T1-E3	SI1031X-T1-GE3	SI1031X-T1-GE3	SI1032R-T1
SI1032R-T1-E3	SI1032R-T1-E3	SI1032R-T1-GE3	SI1032R-T1-GE3	SI1032X-T1

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